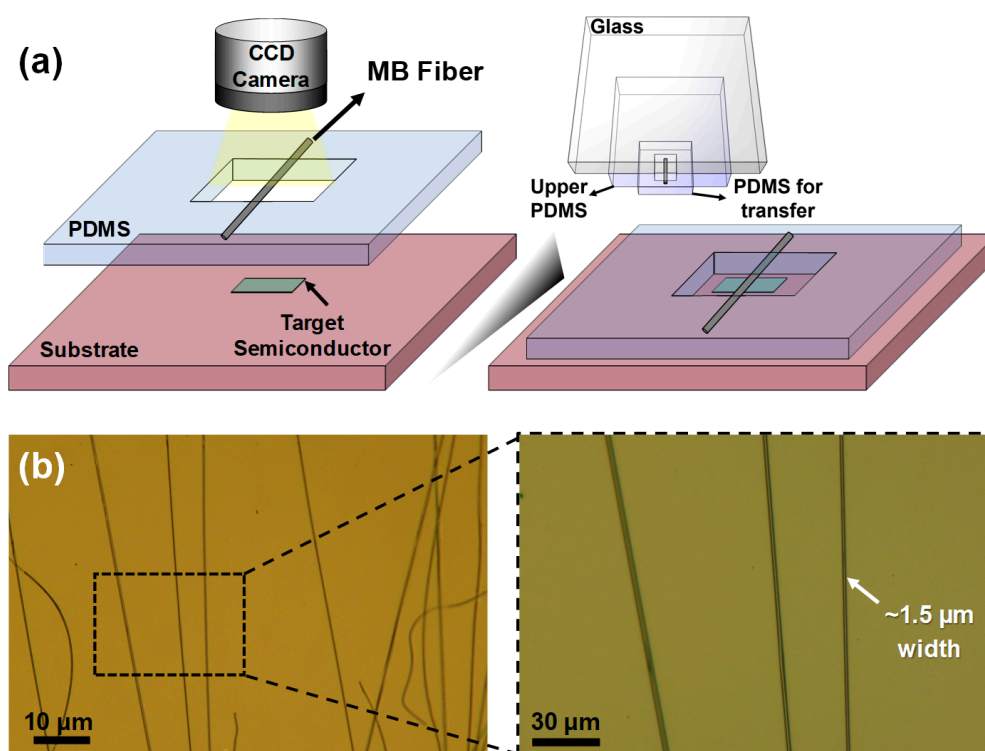


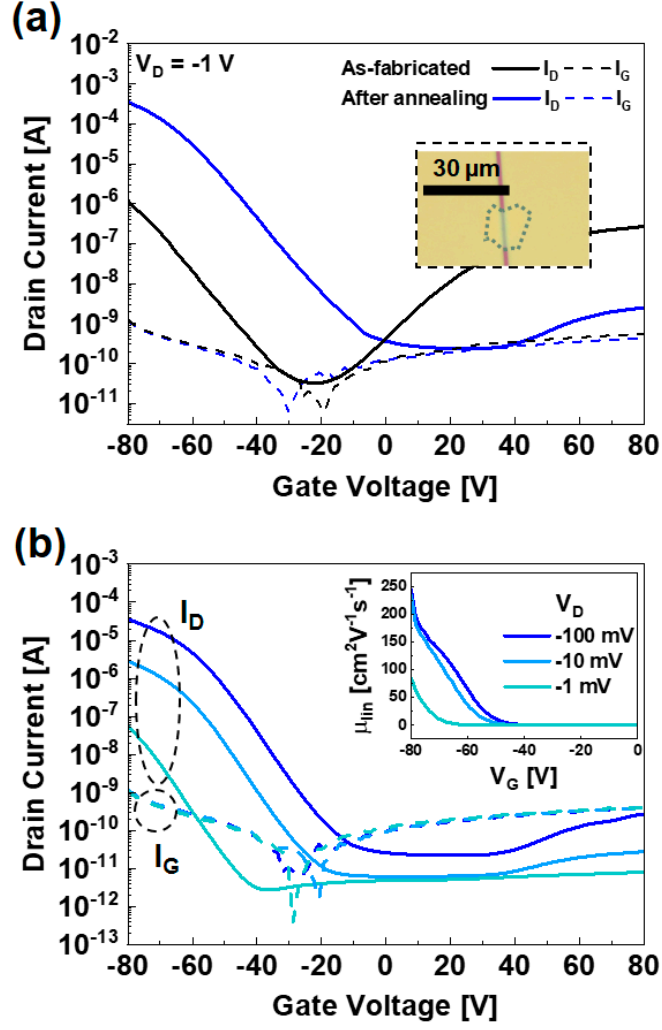
# Supplementary Materials: Melt Blown Fiber-Assisted Solvent-Free Device Fabrication at Low-Temperature

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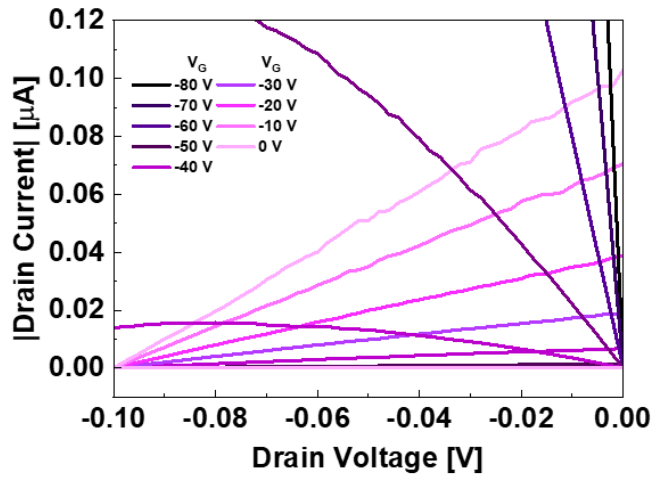
## Experimental Information



**Figure S1.** (a) MB fiber-based shadow masking technique which aligned under the OM system and subsequently attaching on the target semiconductor channel; (b) OM images of the MB fiber. The MB was extracted from a commercial MB filter (MB filter, Yu Han Greentech).



**Figure S2.** (a) Transfer characteristic curves of the WSe<sub>2</sub> PMOS before (as-fabricated) and after the post-annealing process at  $V_D$  of -1 V ( $W/L = 9$ ); (b) Transfer characteristic curves and linear mobility plot (inset) of the post-annealed WSe<sub>2</sub> PMOS at  $V_D$  of -1 mV, -10 mV, and -100 mV.



**Figure S3.** The load-line analysis based on MoS<sub>2</sub> NMOS and WSe<sub>2</sub> PMOS for CMOS inverter circuit.